Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	438/673.ccls. and (pattern near conductive) and photoresist and dielectric and "ion etch".clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 14:02
S1	8	(("6498092") or ("6309957") or ("5512514") or ("4182636")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/17 11:16
S2	0	S1 and deposit$4 and photoresist and pattern$4 and layer and mask$4 and protect$4 and (dielectric or insulat$4) and coat$4 and "ion etch$4" and remov$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/17 11:18
S3	0	deposit$4 and photoresist and pattern$4 and layer and mask$4 and protect$4 and (dielectric or insulat$4) and coat$4 and "ion etch$4" and remov$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 11:18
S4	1340	deposit$4 and photoresist and pattern$4 and layer and mask$4 and protect$4 and dielectric and coat$4 and (ion near4 etch) and remov$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 11:19
S5	783	deposit$4 and photoresist and pattern$4 and layer and mask$4 and protect$4 and dielectric and coat$4 and (ion near4 etch) and remov$4 and relative	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 11:19
S6	574	deposit$4 and photoresist and pattern$4 and layer and mask$4 and protect$4 and dielectric and coat$4 and (ion near4 etch) and remov$4 and relative and via	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 11:19
S7	259	deposit$4 and photoresist and pattern$4 and layer and mask$4 and protect$4 and dielectric and coat$4 and (ion near4 etch) and remov$4 and relative and via and anGLE	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 11:20

S8	0	deposit$4 and photoresist and pattern$4 and layer and mask$4 and protect$4 and dielectric and coat$4 and (ion near4 etch) and remov$4 and relative and via and angle and (wafer or substrate or semiconductor) and conduct$4 and metal and juction and contact	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 11:23
S9	94	deposit$4 and photoresist and pattern$4 and layer and mask$4 and protect$4 and dielectric and coat$4 and (ion near4 etch) and remov$4 and relative and via and angle and (wafer or substrate or semiconductor) and conduct$4 and metal and junction and contact	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 11:25
S10	4	deposit$4 and photoresist and pattern$4 and layer and mask$4 and protect$4 and dielectric and coat$4 and (ion near4 etch) and remov$4 and relative and via and angle and (wafer or substrate or semiconductor) and conduct$4 and metal and junction and contact and magnetic and tunnel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 11:24
S11	40	deposit$4 and photoresist and pattern$4 and layer and mask$4 and protect$4 and dielectric and coat$4 and (ion near4 etch) and remov$4 and relative and via and angle and (wafer or substrate or semiconductor) and conduct$4 and metal and junction and contact and directional	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 12:28
S12	11	(semiconductor or substrate or wafer) and conduct$4 and (deposit near4 photoresist) and mask and protect$4 and dielectric and "ion etching" and angle and via	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 11:53
S13	371	(substrate or wafer or semiconductor) and photoresist and pattern and mask$4 and protect and dielectric and deposit and (ion near4 etch$4) and angle and via	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 12:30
S14	351	(substrate or wafer or semiconductor) and photoresist and pattern and mask$4 and protect and dielectric and deposit and (ion near4 etch$4) and angle and via and conduct$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 12:30

S15	172	(substrate or wafer or semiconductor) and photoresist and pattern and mask$4 and protect and dielectric and deposit and (ion near4 etch$4) and angle and via and conduct$4 and junction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 12:30
S16	74	(substrate or wafer or semiconductor) and photoresist and pattern and mask$4 and protect and dielectric and deposit and (ion near4 etch$4) and angle and via and conduct$4 and junction and stack	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 13:11
S17	55	deposit and photoresist and "patterned layer" and mask$4 and protect and dielectric and "ion etching" and angle	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 14:24
S18	77	photoresist and "patterned layer" and mask$4 and protect and dielectric and "ion etching" and angle	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 08:30
S19	0	photoresist and "patterned layer" and mask$4 and protect and dielectric and "ion etching" and angle and "ion mill$4"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 15:06
S20	5	photoresist and "patterned layer" and mask$4 and protect and dielectric and "ion etching" and angle and "ion milling"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 15:06
S21	1	photoresist and "patterned layer" and mask$4 and protect and dielectric and "ion etching" and angle and "ion milling" and tunnel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 15:07
S22	9003	"ion milling" or "ion beam etching" and "magnetic tunnel junction" and stack$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 08:34

S23	8984	"ion milling" or "ion beam etching" and "magnetic tunnel junction" and stack$4 and photoresist and "patterned layer" and mask$4 and dielectric and "ion etching"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 08:37
S24	8984	"ion milling" or "ion beam etching" and "magnetic tunnel junction" and stack$4 and photoresist and "patterned layer" and mask$4 and dielectric and "ion etching" and angle and protect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 08:38
S25	1	("ion milling" or "ion beam etching") and "magnetic tunnel junction" and stack$4 and photoresist and "patterned layer" and mask$4 and dielectric and "ion etching" and angle and protect and deposit$4 and conduct$4 and row	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 08:39
S26	1	("ion milling" or "ion beam etching") and "magnetic tunnel junction" and stack$4 and photoresist and "patterned layer" and mask$4 and dielectric and "ion etching" and angle and protect and deposit$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 08:39
S27	1	("ion milling" or "ion beam etching") and "magnetic tunnel junction" and stack$4 and photoresist and "patterned layer" and mask$4 and dielectric and "ion etching" and angle and protect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 08:39
S28	125	("ion milling" or "ion beam etching") and "magnetic tunnel junction" and stack$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 08:40
S29	33	("ion milling" or "ion beam etching") and "magnetic tunnel junction" and stack$4 and conduct$4 and row	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 08:40
S30	20	("ion milling" or "ion beam etching") and "magnetic tunnel junction" and stack$4 and conduct$4 and row and ferromagnetic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 11:56

S31	433	(photoresist near layer) and mask and dielectric and "ion etch" and parallel and (via or trench or hole)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:03
S32	0	(photoresist near layer) and mask and dielectric and "ion etch" and parallel and (via or trench or hole) and "low angle"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:03
S33	433	(photoresist near layer) and mask and dielectric and "ion etch" and parallel and (via or trench or hole) and parallel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:03
S34	83	(photoresist near layer) and mask and dielectric and "ion etch" and parallel and (via or trench or hole) and directional	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:11
S35	0	(photoresist near "conductive layer") and (mask or photoresist) and dielectric and "ion etch" and parallel and (via or trench or hole) and directional	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:12
S36	6	(photoresist near ("conductive layer" or metal)) and (mask or photoresist) and dielectric and "ion etch" and parallel and (via or trench or hole) and directional	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:37
S37	912	438/669.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:37
S38	67	438/669.ccls. and (pattern near conductive)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:38

S39	37	438/669.ccls. and (pattern near conductive) and photoresist	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:38
S40	2	438/669.ccls. and (pattern near conductive) and photoresist and dielectric and "ion etch"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:47
S41	2	438/670.ccls. and (pattern near conductive) and photoresist and dielectric and "ion etch"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 13:00
S42	0	438/673.ccls. and (pattern near conductive) and photoresist and dielectric and "ion etch"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 14:02

Interference Search

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	438/673.ccls. and (pattern near conductive) and photoresist and dielectric and "ion etch".clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 14:09
L2	0	438/673.ccls. and (pattern near conductive) and photoresist and dielectric and "ion etch".clm.	US-PGPUB	OR	ON	2005/07/22 14:04
L3	5	(pattern near conductive) and photoresist and dielectric and "ion etch".clm.	US-PGPUB	OR	ON	2005/07/22 14:04
L4	140	438/673.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 14:10